

HAT2141H

Silicon N Channel Power MOS FET
Power Switching

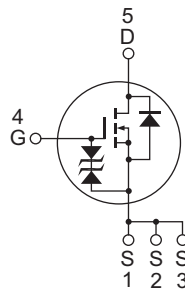
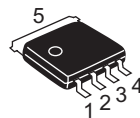
REJ03G1193-0700
(Previous: ADE-208-1582E)
Rev.7.00
Sep 07, 2005

Features

- Capable of 7 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
 $R_{DS(on)} = 22 \text{ m}\Omega$ typ. (at $V_{GS} = 10 \text{ V}$)

Outline

RENESAS Package code: PTZZ0005DA-A
(Package name: LFAK)



1, 2, 3 Source
4 Gate
5 Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V_{DSS}	100	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	15	A
Drain peak current	$I_{D(pulse)}$ ^{Note 1}	60	A
Body-drain diode reverse drain current	I_{DR}	15	A
Avalanche current	I_{AP} ^{Note 3}	15	A
Avalanche energy	E_{AR} ^{Note 3}	22.5	mJ
Channel dissipation	P_{ch} ^{Note 2}	20	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

- Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
 2. $T_c = 25^\circ C$
 3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50 \Omega$

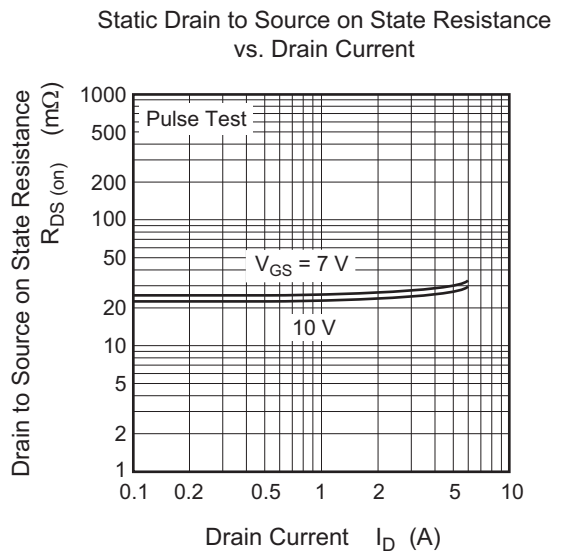
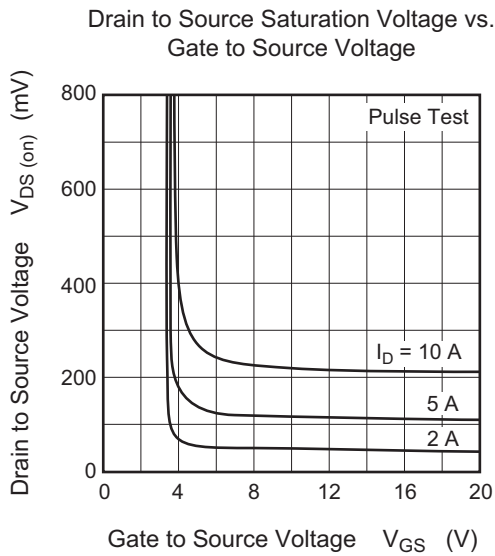
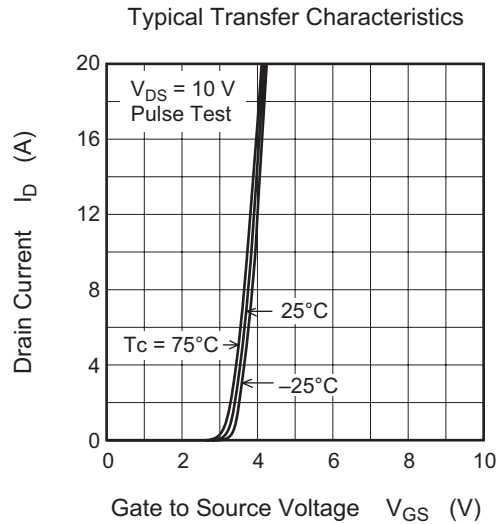
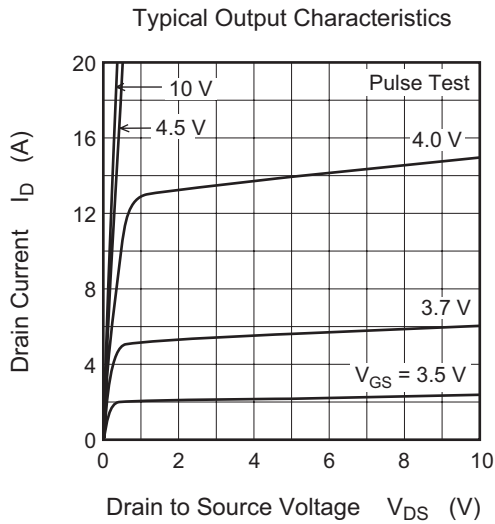
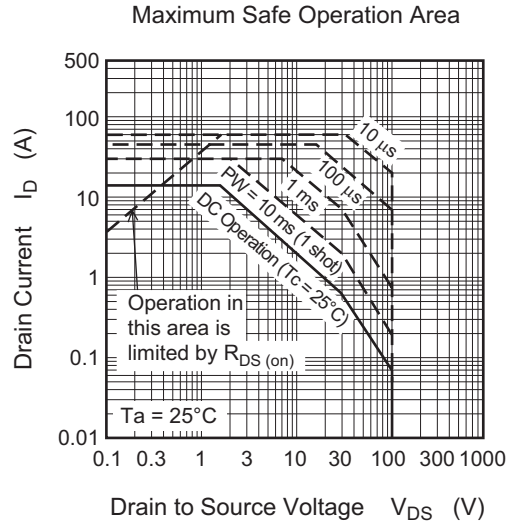
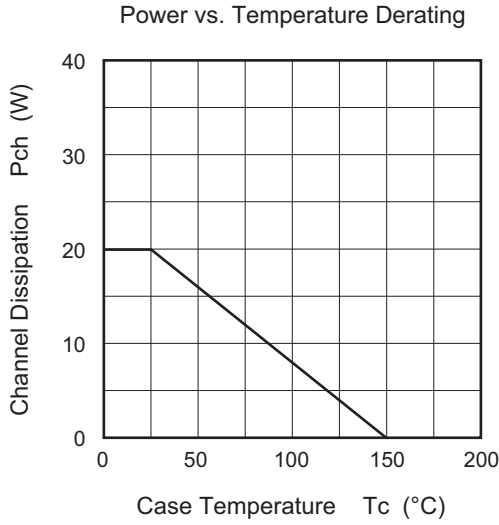
Electrical Characteristics

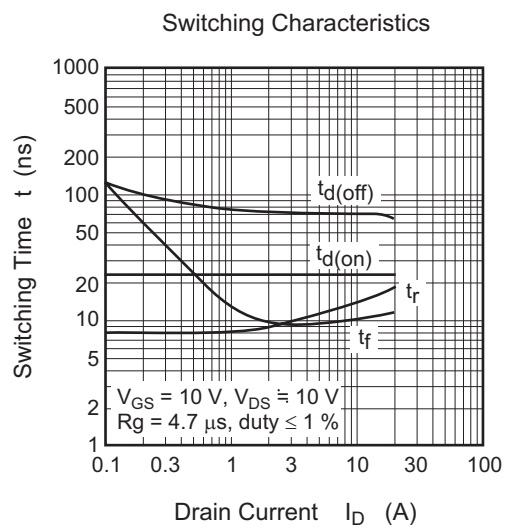
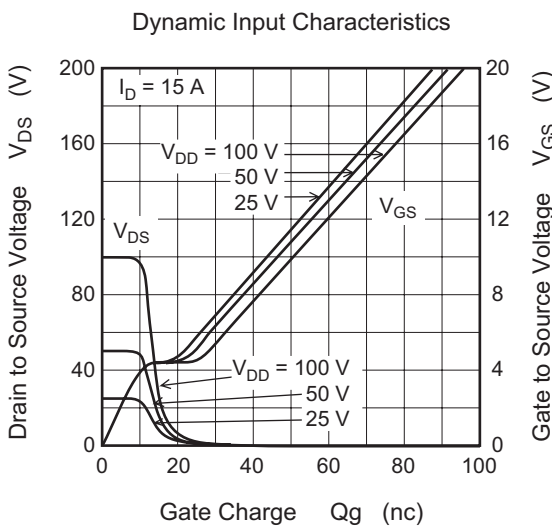
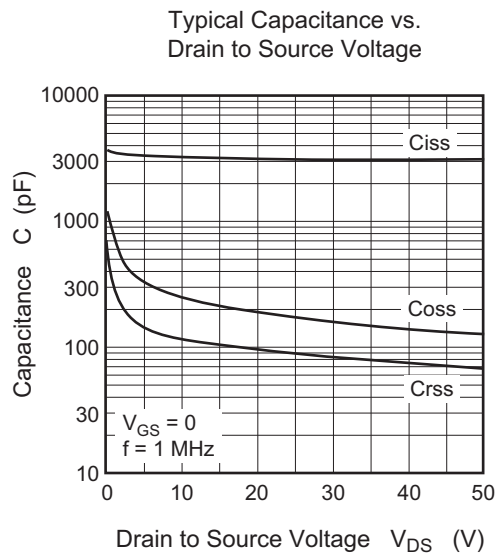
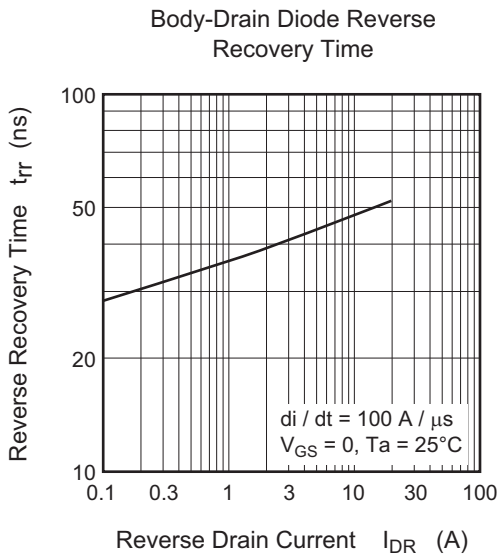
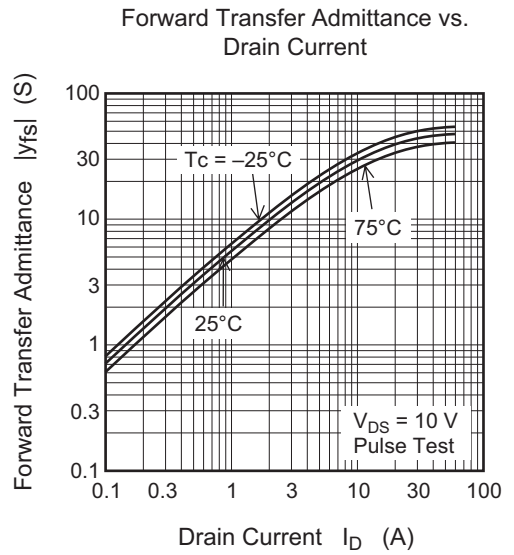
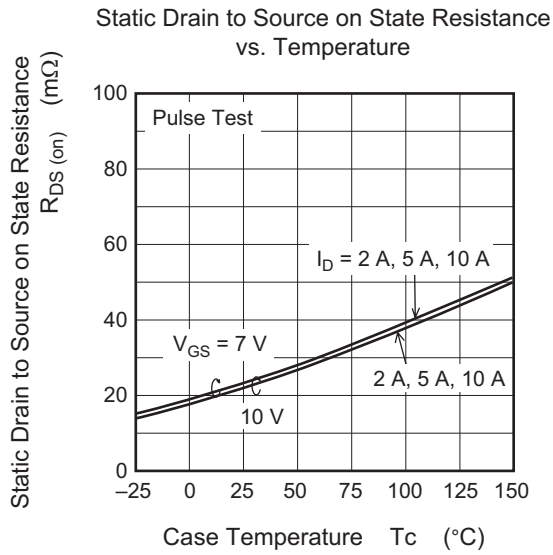
(Ta = 25°C)

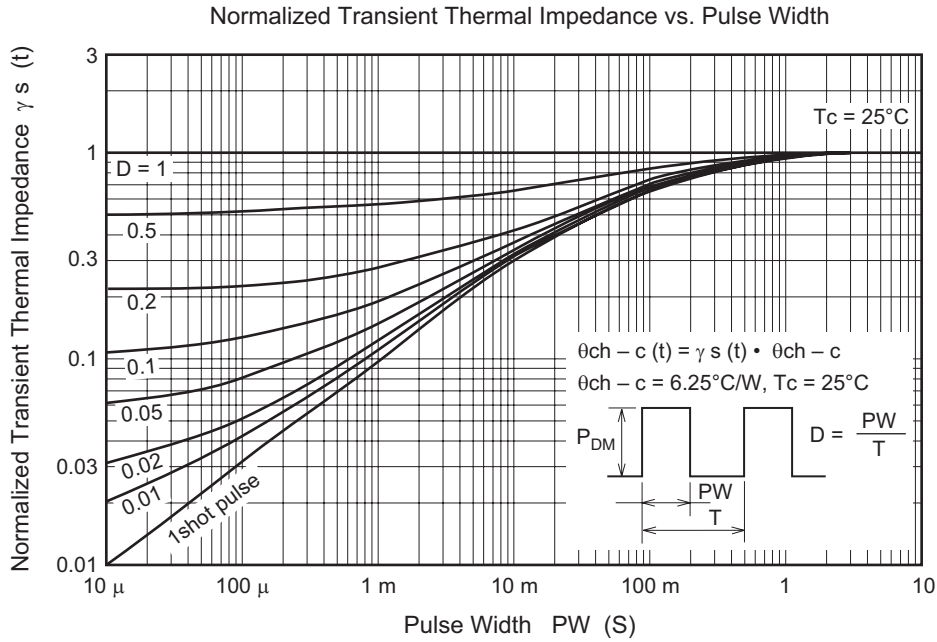
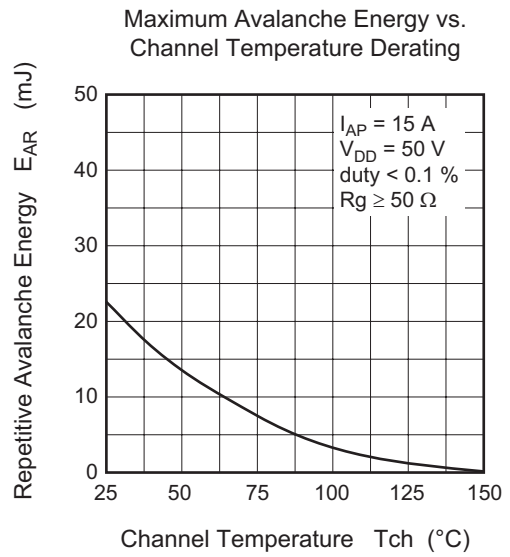
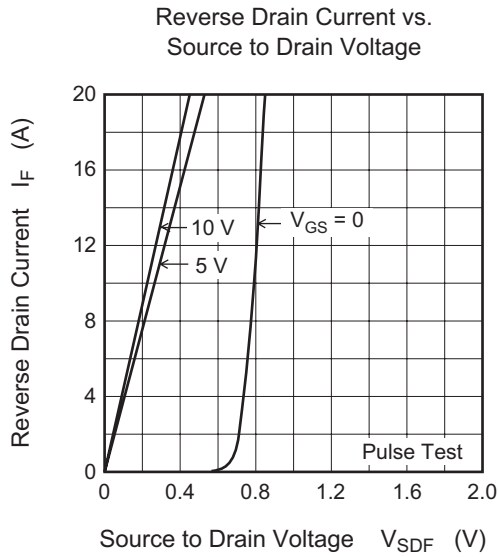
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 100 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	22	27.5	mΩ	$I_D = 7.5 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note 4}
	$R_{DS(on)}$	—	23.5	32	mΩ	$I_D = 7.5 \text{ A}$, $V_{GS} = 7 \text{ V}$ ^{Note 4}
Forward transfer admittance	$ y_{fs} $	15	25	—	S	$I_D = 7.5 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note 4}
Input capacitance	C_{iss}	—	3200	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	255	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	125	—	pF	$f = 1 \text{ MHz}$
Total gate charge	Q_g	—	46	—	nC	$V_{DD} = 50 \text{ V}$
Gate to source charge	Q_{gs}	—	11	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Q_{gd}	—	10	—	nC	$I_D = 15 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	22	—	ns	$V_{GS} = 10 \text{ V}$, $I_D = 7.5 \text{ A}$
Rise time	t_r	—	13	—	ns	$V_{DD} \cong 30 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	70	—	ns	$R_L = 4 \Omega$
Fall time	t_f	—	10	—	ns	$R_g = 4.7 \Omega$
Body-drain diode forward voltage	V_{DF}	—	0.82	1.07	V	$I_F = 15 \text{ A}$, $V_{GS} = 0$ ^{Note 4}
Body-drain diode reverse recovery time	t_{rr}	—	50	—	ns	$I_F = 15 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu s$

Note: 4. Pulse test

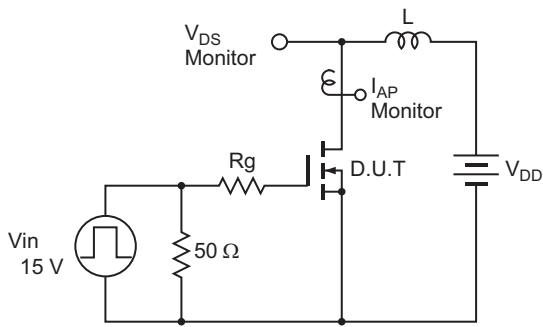
Main Characteristics



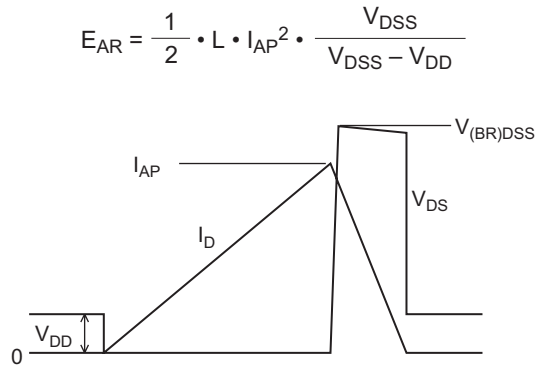


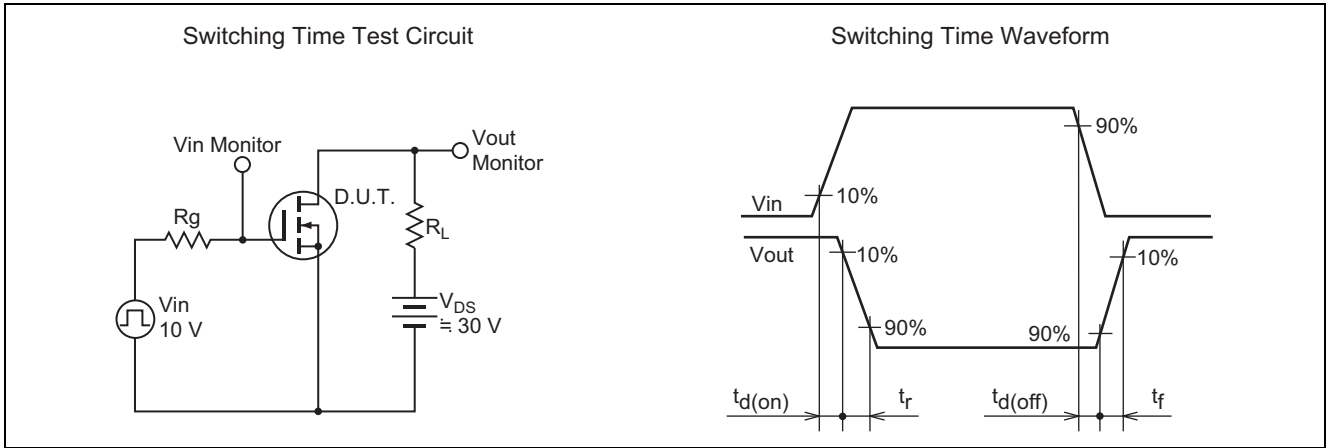


Avalanche Test Circuit

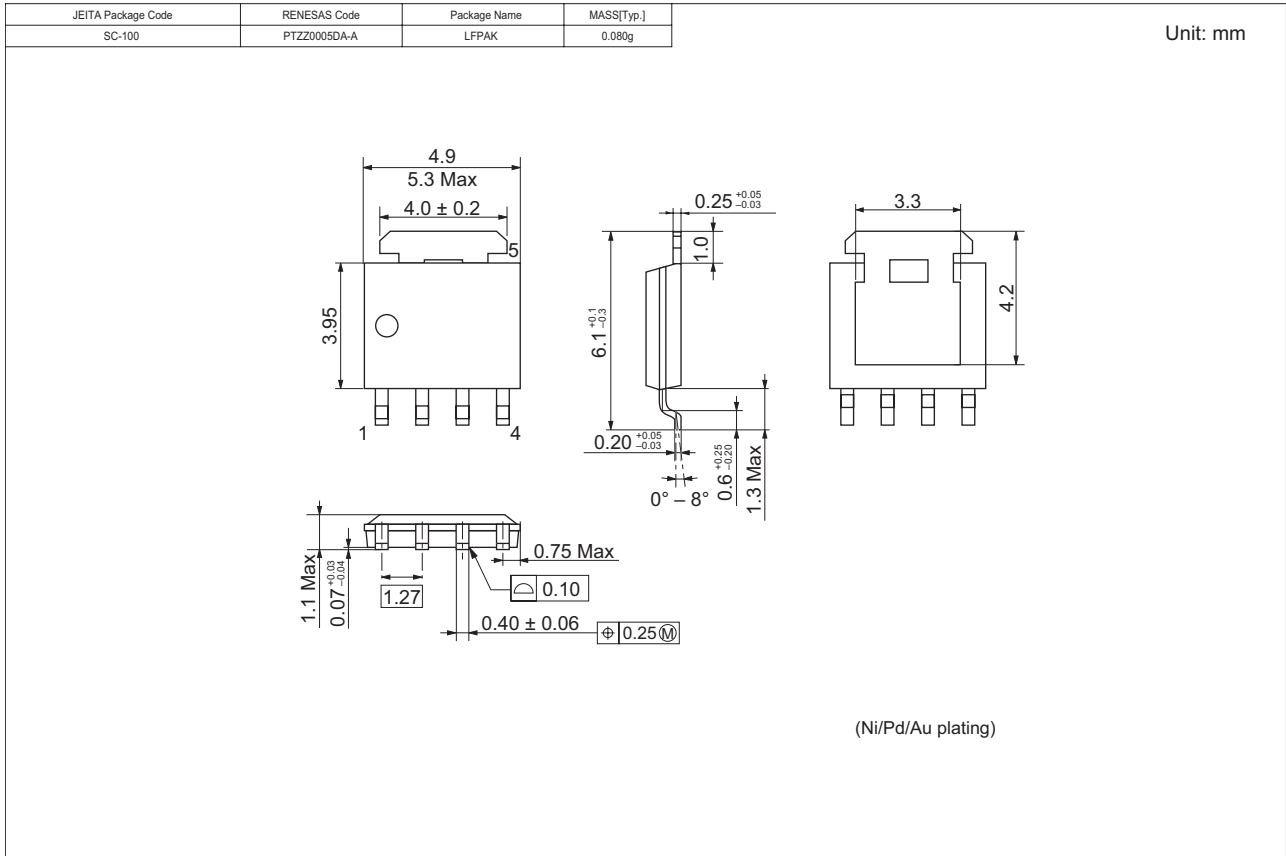


Avalanche Waveform





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT2141H-EL-E	2500 pcs	Taping

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